

FEATURES :

- LOW INTERMODULATION DISTORTION
IM₃ = -45 dBc at Po = 34.5 dBm
Single Carrier Level
- HIGH POWER
P_{1dB} = 45 dBm at 6.4 GHz to 7.2 GHz
- HIGH EFFICIENCY
η_{add} = 36 % at 6.4 GHz to 7.2 GHz
- HIGH GAIN
G_{1dB} = 7.0 dB at 6.4 GHz to 7.2 GHz
- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB Compression Point	P _{1dB}	V _{DS} = 10 V f = 6.4 ~ 7.2 GHz	dBm	44.0	45.0	—
Power Gain at 1 dB Compression Point	G _{1dB}		dB	6.0	7.0	—
Drain Current	I _{DS}		A	—	7.0	8.0
Power Added Efficiency	η _{add}		%	—	36	—
3rd Order Intermodulation Distortion	IM ₃	Note 1	dBc	-42	-45	—
Channel-Temperature Rise	ΔT _{ch}	V _{DS} × I _{DS} × R _{th} (c-c)	°C	—	—	100

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	V _{DS} = 3 V I _{DS} = 10 A	mS	—	6300	—
Pinch-off Voltage	V _{GSoff}	V _{DS} = 3 V I _{DS} = 100 mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	I _{DSS}	V _{DS} = 3 V V _{GS} = 0 V	A	—	18	22
Gate-Source Breakdown Voltage	V _{GS0}	I _{GS} = -350 μA	V	-5	—	—
Thermal Resistance	R _{th} (c-c)	Channel to Case	°C/W	—	1.0	1.3

Note 1 : 2 tone Test Pout = 34.5 dBm Single Carrier Level.

Recommended Gate Resistance(R_g) : R_g = R_{g1}(10 Ω) + R_{g2}(18 Ω) = 28 Ω (MAX.)

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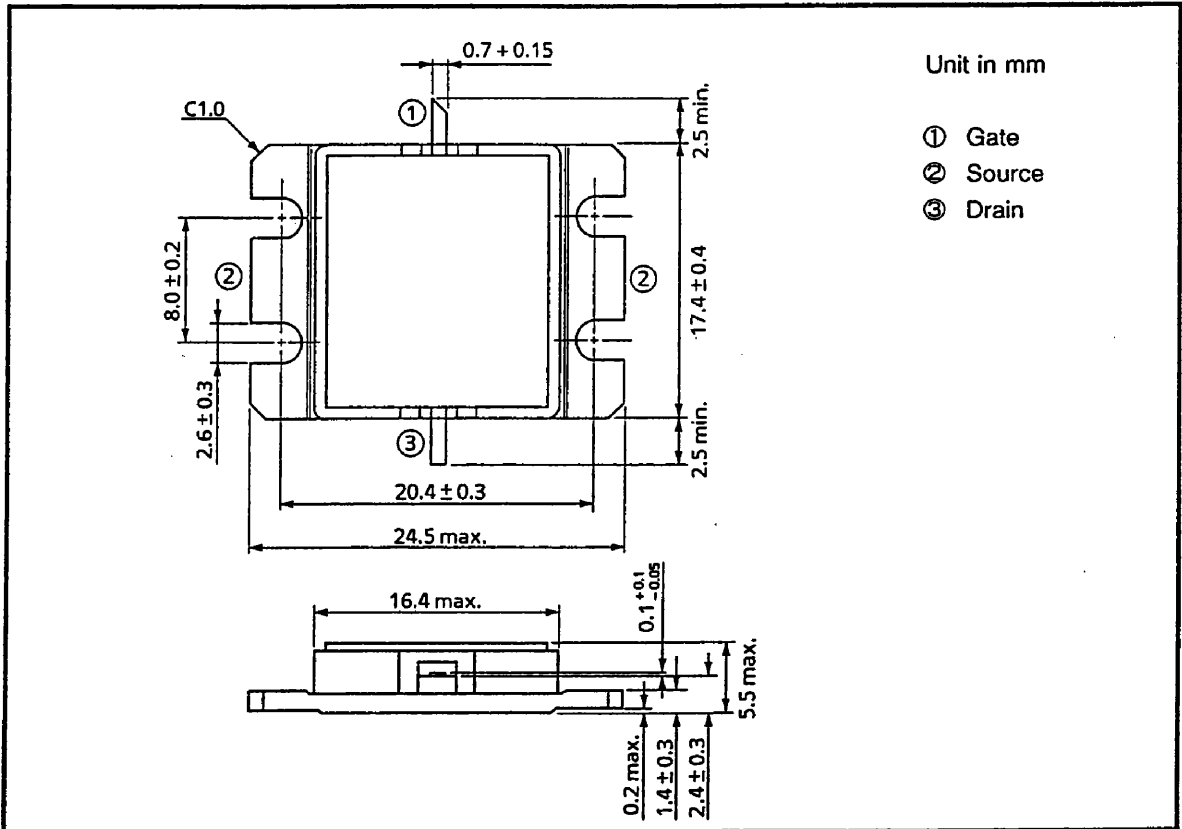


TIM6472-30SL

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	22
Total Power Dissipation (T _C = 25°C)	P _T	W	115
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

PACKAGE OUTLINE (2-16G1B)

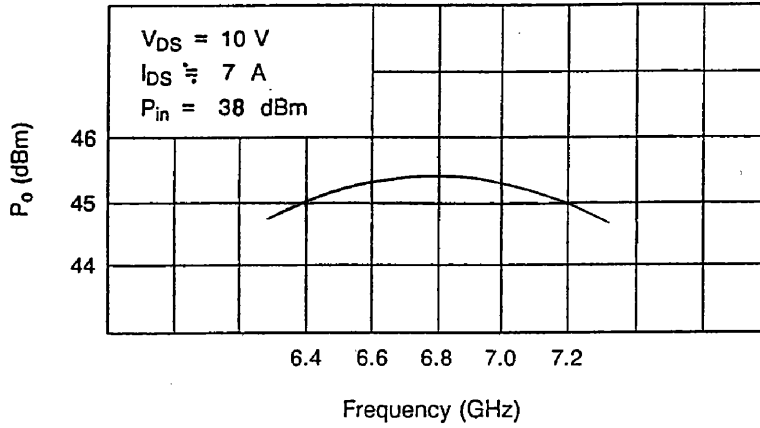


HANDLING PRECAUTIONS FOR PACKAGED TYPE

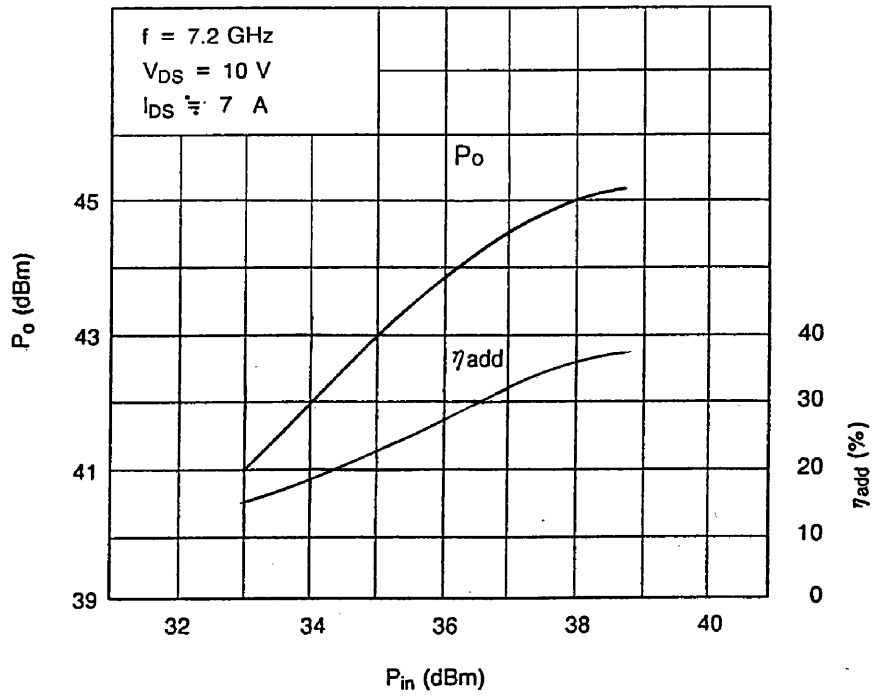
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCES

Output Power vs. Frequency

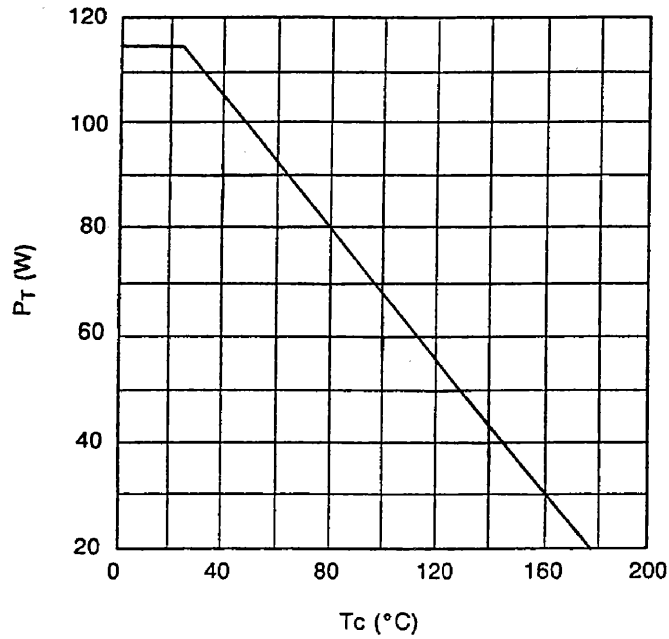


Output Power vs. Input Power



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POWER DISSIPATION VS. CASE TEMPERATURE



IM₃ VS. OUTPUT POWER CHARACTERISTICS

